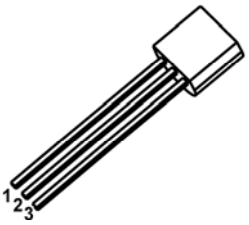
TO-92 Plastic-Encapsulate Transistors

TO – 92

1. EMITTER
2. BASE
3. COLLECTOR



2SB1426 TRANSISTOR (PNP)

FEATURES

- General Purpose Switching and Amplification

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-20	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-3	A
P_C	Collector Power Dissipation	750	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	166	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -0.05mA,I_E=0	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.05mA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-2V, I_C=-0.1A	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=-2A,I_B=-0.1A			-0.5	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz		35		pF
Transition frequency	f_T	V_{CE}=-2V,I_C=-0.5A, f=100MHz		240		MHz

*Pulse test

CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390